

### 30A, 1000V Hyperfast Diode

The RHRP30100 is a hyperfast diode with soft recovery characteristics ( $t_{rr} < 65\text{ns}$ ). It has half the recovery time of ultrafast diodes and is of silicon nitride passivated ion-implanted epitaxial planar construction.

This device is intended for use as a freewheeling/clamping diode and rectifier in a variety of switching power supplies and other power switching applications. Its low stored charge and hyperfast soft recovery minimize ringing and electrical noise in many power switching circuits, thus reducing power loss in the switching transistors.

### Ordering Information

PART NUMBER	PACKAGE
RHRP30100	TO-220AC

### Symbol



### Features

- Hyperfast with Soft Recovery ..... <65ns
- Operating Temperature ..... 175°C
- Reverse Voltage ..... 1000V
- Avalanche Energy Rated
- Planar Construction

### Applications

- Switching Power Supplies
- Power Switching Circuits
- General Purpose

### Packaging



1.CATHODE  
2.ANODE

### Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ , Unless Otherwise Specified

	RHRP30100	UNITS
Peak Repetitive Reverse Voltage .....	$V_{RRM}$ 1000	V
Working Peak Reverse Voltage .....	$V_{RWM}$ 1000	V
DC Blocking Voltage .....	$V_R$ 1000	V
Average Rectified Forward Current .....	$I_{F(AV)}$ 30	A
( $T_C = 95^\circ\text{C}$ )		
Repetitive Peak Surge Current .....	$I_{FRM}$ 70	A
(Square Wave, 20kHz)		
Nonrepetitive Peak Surge Current .....	$I_{FSM}$ 325	A
(Halfwave, 1 Phase, 60Hz)		
Maximum Power Dissipation .....	$P_D$ 125	W
Avalanche Energy (See Figures 10 and 11) .....	$E_{AVL}$ 20	mJ
Operating and Storage Temperature .....	$T_{STG}, T_J$ -65 to 175	°C

**Electrical Specifications**  $T_C = 25^\circ\text{C}$ , Unless Otherwise Specified

SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNITS
$V_F$	$I_F = 30\text{A}$	-	-	3.0	V
	$I_F = 30\text{A}, T_C = 150^\circ\text{C}$	-	-	2.5	V
$I_R$	$V_R = 1000\text{V}$	-	-	250	$\mu\text{A}$
	$V_R = 1000\text{V}, T_C = 150^\circ\text{C}$	-	-	1.0	$\text{mA}$
$t_{rr}$	$I_F = 1\text{A}, dI_F/dt = 100\text{A}/\mu\text{s}$	-	-	65	ns
	$I_F = 30\text{A}, dI_F/dt = 100\text{A}/\mu\text{s}$	-	-	75	ns
$t_a$	$I_F = 30\text{A}, dI_F/dt = 100\text{A}/\mu\text{s}$	-	35	-	ns
$t_b$	$I_F = 30\text{A}, dI_F/dt = 100\text{A}/\mu\text{s}$	-	33	-	ns
$Q_{RR}$	$I_F = 30\text{A}, dI_F/dt = 100\text{A}/\mu\text{s}$	-	200	-	nC
$C_J$	$V_R = 10\text{V}, I_F = 0\text{A}$	-	100	-	pF
$R_{\theta JC}$		-	-	1.2	$^\circ\text{C}/\text{W}$

DEFINITIONS

$V_F$  = Instantaneous forward voltage (pw = 300 $\mu\text{s}$ , D = 2%).

$I_R$  = Instantaneous reverse current.

$t_{rr}$  = Reverse recovery time (Figure 9), summation of  $t_a + t_b$ .

$t_a$  = Time to reach peak reverse current (See Figure 9).

$t_b$  = Time from peak  $I_{RM}$  to projected zero crossing of  $I_{RM}$  based on a straight line from peak  $I_{RM}$  through 25% of  $I_{RM}$  (See Figure 9).

$Q_{RR}$  = Reverse recovery charge.

$C_J$  = Junction Capacitance.

$R_{\theta JC}$  = Thermal resistance junction to case.

pw = pulse width.

D = duty cycle.

**Typical Performance Curves**

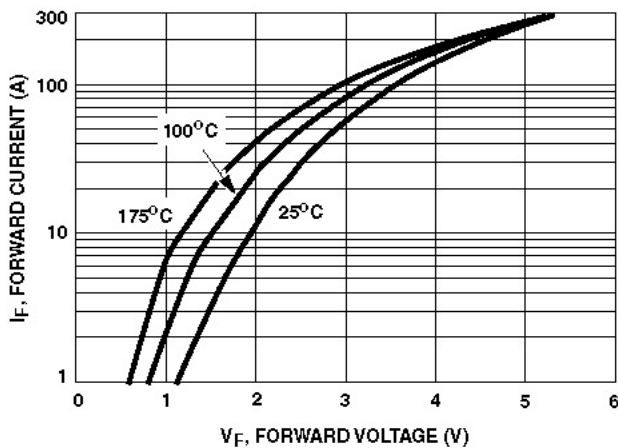


FIGURE 1. FORWARD CURRENT vs FORWARD VOLTAGE

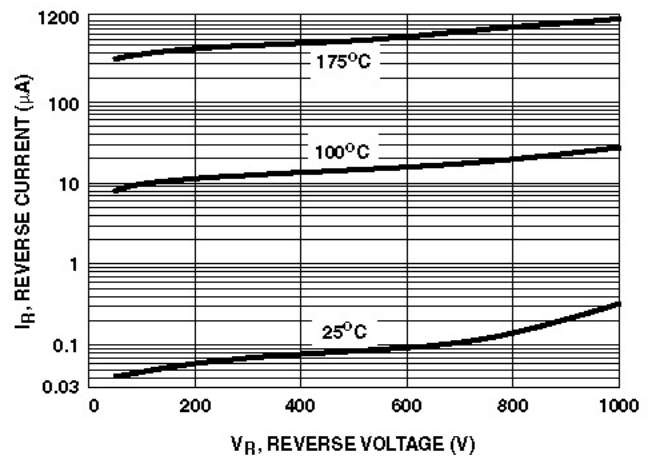


FIGURE 2. REVERSE CURRENT vs REVERSE VOLTAGE

Typical Performance Curves (Continued)

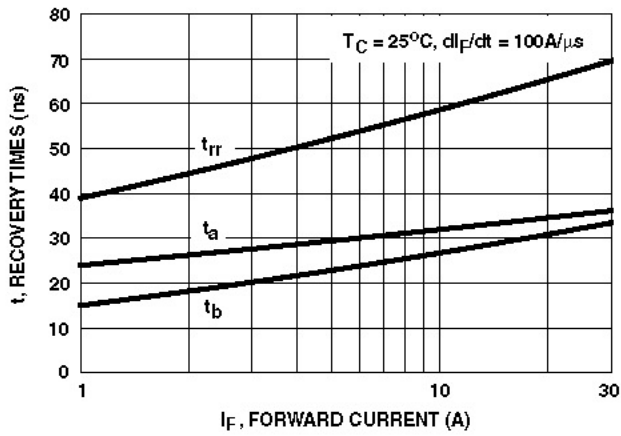


FIGURE 3.  $t_{rr}$ ,  $t_a$  AND  $t_b$  CURVES vs FORWARD CURRENT

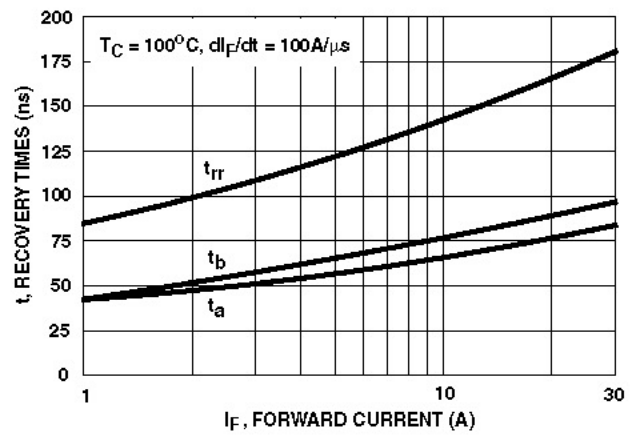


FIGURE 4.  $t_{rr}$ ,  $t_a$  AND  $t_b$  CURVES vs FORWARD CURRENT

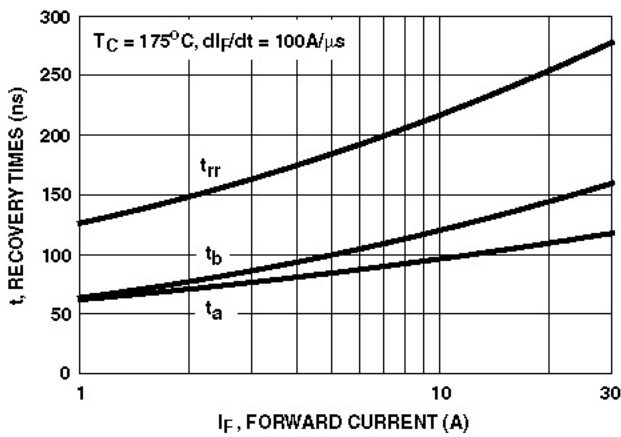


FIGURE 5.  $t_{rr}$ ,  $t_a$  AND  $t_b$  CURVES vs FORWARD CURRENT

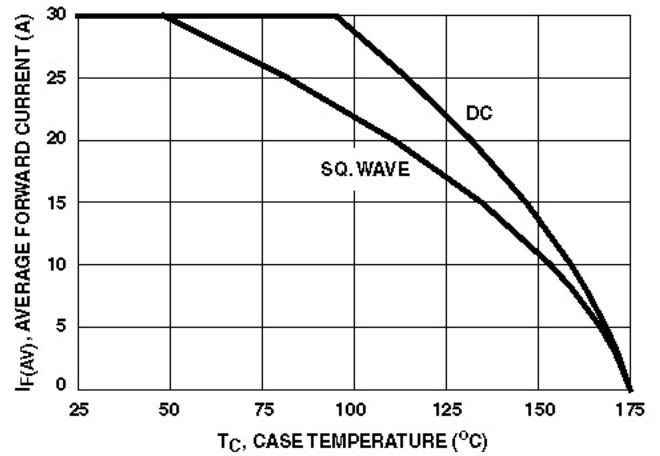


FIGURE 6. CURRENT DERATING CURVE

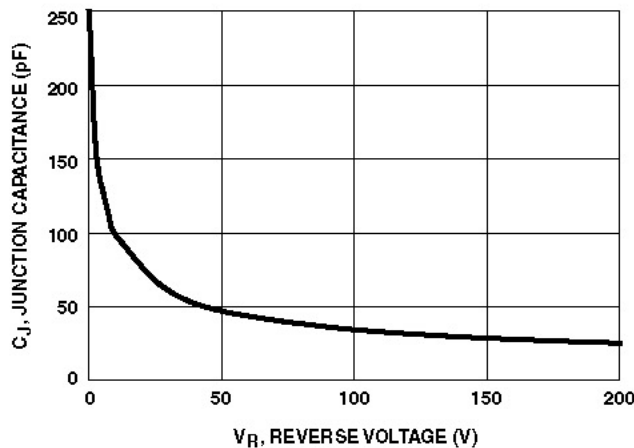


FIGURE 7. JUNCTION CAPACITANCE vs REVERSE VOLTAGE

**Test Circuits and Waveforms**

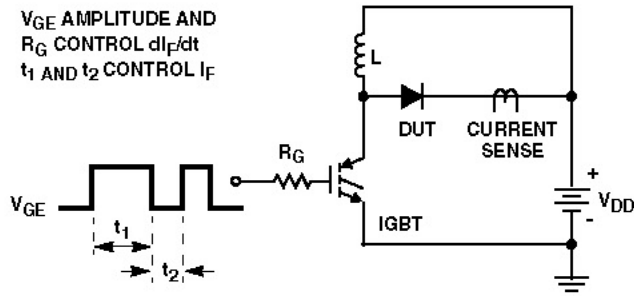


FIGURE 8.  $t_{rr}$  TEST CIRCUIT

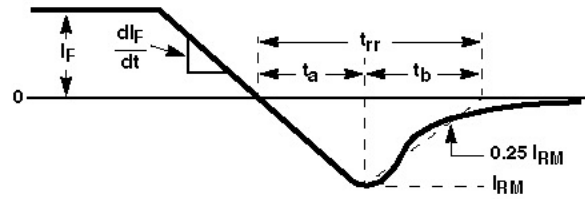


FIGURE 9.  $t_{rr}$  WAVEFORMS AND DEFINITIONS

$I_{MAX} = 1A$   
 $L = 40mH$   
 $R < 0.1\Omega$   
 $E_{AVL} = 1/2LI^2 [V_{R(AVL)}/(V_{R(AVL)} - V_{DD})]$   
 $Q_1 = IGBT (BV_{CES} > DUT V_{R(AVL)})$

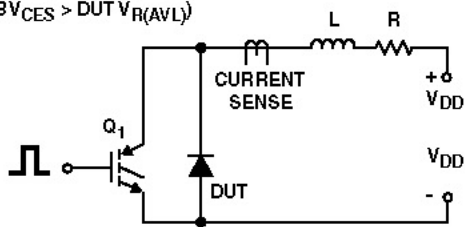


FIGURE 10. AVALANCHE ENERGY TEST CIRCUIT

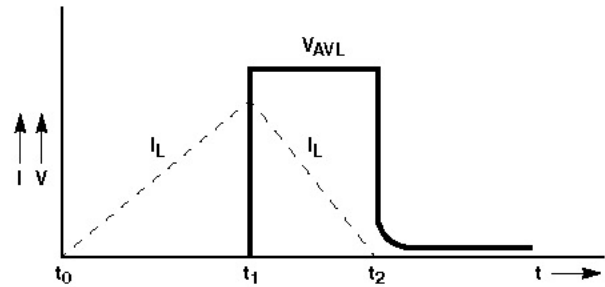


FIGURE 11. AVALANCHE CURRENT AND VOLTAGE WAVEFORMS